

Z R Kudrynskyi

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

68

papers

2,381

citations

18

h-index

48

g-index

73

ext. papers

2,880

ext. citations

6

avg, IF

4.61

L-index

#	Paper	IF	Citations
68	Characterization of potential nanoporous sodium titanate film formation on Ti6Al4V and TiO ₂ microspherical substrates via wet-chemical alkaline conversion. <i>Materials Characterization</i> , 2022 , 185, 111760	3.9	2
67	Terahertz control of photoluminescence emission in few-layer InSe. <i>Applied Physics Letters</i> , 2022 , 120, 092104	3.4	0
66	Large Tunneling Magnetoresistance in van der Waals Ferromagnet/Semiconductor Heterojunctions. <i>Advanced Materials</i> , 2021 , e2104658	24	10
65	Charge Carrier Transport in Van Der Waals Semiconductor InSe Intercalated with RbNO ₃ Probed by Direct Current Methods. <i>Applied Sciences (Switzerland)</i> , 2021 , 11, 5181	2.6	
64	Inter-Flake Quantum Transport of Electrons and Holes in Inkjet-Printed Graphene Devices. <i>Advanced Functional Materials</i> , 2021 , 31, 2007478	15.6	13
63	Anomalous Low Thermal Conductivity of Atomically Thin InSe Probed by Scanning Thermal Microscopy. <i>Advanced Functional Materials</i> , 2021 , 31, 2008967	15.6	4
62	Ferroelectric semiconductor junctions based on graphene/In ₂ Se ₃ /graphene van der Waals heterostructures. <i>2D Materials</i> , 2021 , 8, 045020	5.9	4
61	Tunable spin-orbit coupling in two-dimensional InSe. <i>Physical Review B</i> , 2021 , 104,	3.3	2
60	Resonance and antiresonance in Raman scattering in GaSe and InSe crystals. <i>Scientific Reports</i> , 2021 , 11, 924	4.9	2
59	Enhanced Optical Emission from 2D InSe Bent onto Si-Pillars. <i>Advanced Optical Materials</i> , 2020 , 8, 2000828	3.8	10
58	The Interaction of Hydrogen with the van der Waals Crystal -InSe. <i>Molecules</i> , 2020 , 25,	4.8	8
57	Interlayer Band-to-Band Tunneling and Negative Differential Resistance in van der Waals BP/InSe Field-Effect Transistors. <i>Advanced Functional Materials</i> , 2020 , 30, 1910713	15.6	41
56	Resonant tunnelling into the two-dimensional subbands of InSe layers. <i>Communications Physics</i> , 2020 , 3,	5.4	13
55	Design of van der Waals interfaces for broad-spectrum optoelectronics. <i>Nature Materials</i> , 2020 , 19, 299-304	30.4	64
54	Photoluminescence dynamics in few-layer InSe. <i>Physical Review Materials</i> , 2020 , 4,	3.2	7
53	Van der Waals SnSe ₂ (1-x)S ₂ x Alloys: Composition-Dependent Bowing Coefficient and Electron-Phonon Interaction. <i>Advanced Functional Materials</i> , 2020 , 30, 1908092	15.6	10
52	Defect-Assisted High Photoconductive UV-Visible Gain in Perovskite-Decorated Graphene Transistors. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 147-154	4	8

51	High-Frequency Elastic Coupling at the Interface of van der Waals Nanolayers Imaged by Picosecond Ultrasonics. <i>ACS Nano</i> , 2019 , 13, 11530-11537	16.7	15
50	Formation and Healing of Defects in Atomically Thin GaSe and InSe. <i>ACS Nano</i> , 2019 , 13, 5112-5123	16.7	23
49	Two-Dimensional Covalent Crystals by Chemical Conversion of Thin van der Waals Materials. <i>Nano Letters</i> , 2019 , 19, 6475-6481	11.5	26
48	Schottky-barrier thin-film transistors based on HfO ₂ -capped InSe. <i>Applied Physics Letters</i> , 2019 , 115, 033502	5.4	10
47	Photoquantum Hall Effect and Light-Induced Charge Transfer at the Interface of Graphene/InSe Heterostructures. <i>Advanced Functional Materials</i> , 2019 , 29, 1805491	15.6	13
46	Improved performance of InSe field-effect transistors by channel encapsulation. <i>Semiconductor Science and Technology</i> , 2018 , 33, 06LT01	1.8	11
45	Coherent acoustic phonons in van der Waals nanolayers and heterostructures. <i>Physical Review B</i> , 2018 , 98,	3.3	19
44	Magnetotransport and lateral confinement in an InSe van der Waals Heterostructure. <i>2D Materials</i> , 2018 , 5, 035040	5.9	6
43	Epitaxial growth of InSe and In ₂ Se ₃ on GaSe. <i>2D Materials</i> , 2018 , 5, 035026	5.9	55
42	Gate-Defined Quantum Confinement in InSe-Based van der Waals Heterostructures. <i>Nano Letters</i> , 2018 , 18, 3950-3955	11.5	33
41	Room Temperature Uniaxial Magnetic Anisotropy Induced By Fe-Islands in the InSe Semiconductor Van Der Waals Crystal. <i>Advanced Science</i> , 2018 , 5, 1800257	13.6	5
40	Engineering p-n junctions and bandgap tuning of InSe nanolayers by controlled oxidation. <i>2D Materials</i> , 2017 , 4, 025043	5.9	63
39	Giant Quantum Hall Plateau in Graphene Coupled to an InSe van der Waals Crystal. <i>Physical Review Letters</i> , 2017 , 119, 157701	7.4	33
38	High electron mobility, quantum Hall effect and anomalous optical response in atomically thin InSe. <i>Nature Nanotechnology</i> , 2017 , 12, 223-227	28.7	723
37	Nanomechanical probing of the layer/substrate interface of an exfoliated InSe sheet on sapphire. <i>Scientific Reports</i> , 2016 , 6, 26970	4.9	13
36	Preparation of Nanocomposite Magnetic Compounds Based on Layered Semiconductors by Means of Electrochemical Intercalation in a Gradient Magnetic Field. <i>Acta Physica Polonica A</i> , 2016 , 130, 773-777	0.6	0
35	Physical properties of layered FeIn ₂ Se ₄ single crystals. <i>Functional Materials</i> , 2016 , 23, 557-560	0.6	
34	The direct-to-indirect band gap crossover in two-dimensional van der Waals Indium Selenide crystals. <i>Scientific Reports</i> , 2016 , 6, 39619	4.9	114

33	Highly-mismatched InAs/InSe heterojunction diodes. <i>Applied Physics Letters</i> , 2016 , 109, 182115	3.4	9
32	Quantum confinement and photoresponsivity of In_2Se_3 nanosheets grown by physical vapour transport. <i>2D Materials</i> , 2016 , 3, 025030	5.9	68
31	Biexciton formation and exciton coherent coupling in layered GaSe. <i>Journal of Chemical Physics</i> , 2015 , 142, 212422	3.9	24
30	Photoelectric properties of n-ITO/p-GaTe heterojunctions. <i>Semiconductors</i> , 2015 , 49, 600-603	0.7	1
29	Graphene-InSe-graphene van der Waals heterostructures. <i>Journal of Physics: Conference Series</i> , 2015 , 647, 012001	0.3	9
28	Electrochemical, optical, and magnetic properties of Ni_xGaSe ($0 < x < 1$). <i>Inorganic Materials</i> , 2015 , 51, 1086-1089	0.3	0
27	Fabrication and characterization of photosensitive n-ZnO/p-InSe heterojunctions. <i>Thin Solid Films</i> , 2015 , 582, 253-257	2.2	6
26	Nanocomposite structures grown by inserting ionic salt RbNO_3 into van der Waals gaps of III-VI compound layered semiconductors. <i>Solid State Ionics</i> , 2015 , 273, 59-65	3.3	4
25	High broad-band photoresponsivity of mechanically formed InSe-graphene van der Waals heterostructures. <i>Advanced Materials</i> , 2015 , 27, 3760-6	24	252
24	Fabrication and characterization of PbSe nanostructures on van der Waals surfaces of GaSe layered semiconductor crystals. <i>Nanotechnology</i> , 2015 , 26, 465601	3.4	3
23	Morphology of Van der Waals surfaces and magnetic hysteresis in cobalt intercalated InTe. <i>Functional Materials</i> , 2015 , 22, 327-331	0.6	
22	Structure of oxidized and unoxidized end faces of GaSe layered crystals. <i>Inorganic Materials</i> , 2014 , 50, 339-343	0.9	6
21	Mechanism of excitonic dephasing in layered InSe crystals. <i>Physical Review B</i> , 2014 , 89,	3.3	22
20	Spectral anisotropy of a photoresponse from heterojunctions based on GaSe and InSe layered crystals. <i>Technical Physics</i> , 2014 , 59, 407-410	0.5	4
19	Structure and magnetic properties of cobalt-intercalated layered InSe crystals. <i>Technical Physics</i> , 2014 , 59, 1462-1465	0.5	2
18	Photosensitive anisotype n-ZnSe/p-InSe and n-ZnSe/p-GaSe heterojunctions. <i>Technical Physics</i> , 2014 , 59, 1205-1208	0.5	5
17	Influence of Optical Illumination on the Electric Impedance of Composite Nanostructures Based on p-GaSe Layered Semiconductor with 3D Nanodimensional Inclusions of KNO_3 Ferroelectric. <i>Russian Physics Journal</i> , 2014 , 57, 642-656	0.7	
16	Effect of low-temperature annealing on the quality of InSe layered single crystals and the characteristics of n-InSe/p-InSe heterojunctions. <i>Semiconductors</i> , 2014 , 48, 545-550	0.7	6

15	On the photopleochroism coefficient and its temperature dynamics in native oxide-p-InSe heterojunctions. <i>Semiconductors</i> , 2014 , 48, 776-778	0.7	3
14	Morphology, chemical composition, and electrical characteristics of hybrid (Ni-C) nanocomposite structures grown on the van der Waals GaSe(0001) surface. <i>Physics of the Solid State</i> , 2014 , 56, 2118-2130	0.8	2
13	Room Temperature Electroluminescence from Mechanically Formed van der Waals III-VI Homojunctions and Heterojunctions. <i>Advanced Optical Materials</i> , 2014 , 2, 1064-1069	8.1	61
12	Quantum confined acceptors and donors in InSe nanosheets. <i>Applied Physics Letters</i> , 2014 , 105, 221909	3.4	53
11	Controlled synthesis and characterization of highly ordered core-shell nickel-carbon nanoparticle arrays on the van der Waals surfaces of layered semiconductor crystals. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2014 , 211, 342-350	1.6	6
10	Magnetic properties and surface morphology of layered In ₂ Se ₃ crystals intercalated with cobalt. <i>Physics of the Solid State</i> , 2013 , 55, 1148-1155	0.8	14
9	Electrical and photoelectric properties of n-CdO-p-InSe anisotype heterojunctions. <i>Semiconductors</i> , 2013 , 47, 943-946	0.7	5
8	Optical size effect in In ₂ O ₃ nanostructured films. <i>Semiconductors</i> , 2013 , 47, 345-348	0.7	7
7	Tuning the bandgap of exfoliated InSe nanosheets by quantum confinement. <i>Advanced Materials</i> , 2013 , 25, 5714-8	24	419
6	Sensitive elements of pressure transducers made of layered intercalated InSe, GaSe, and Bi ₂ Te ₃ crystals. <i>Technical Physics</i> , 2013 , 58, 1840-1843	0.5	2
5	Fabrication and Characterization of Photosensitive n-CdO/p-InSe Heterojunctions. <i>Acta Physica Polonica A</i> , 2013 , 124, 720-723	0.6	6
4	Composite Nanostructures Based on a Layered Semiconductor with Nanoscale 3D Ferroelectric Inclusions (p-GaSe Intercalated by KNO ₃). <i>Sensor Letters</i> , 2013 , 11, 1549-1554	0.9	4
3	Surface morphology and electrical properties of Au/Ni/C/n-Ga ₂ O ₃ /p-GaSe<KNO ₃ > hybrid structures fabricated on the basis of a layered semiconductor with nanoscale ferroelectric inclusions. <i>Semiconductors</i> , 2012 , 46, 342-353	0.7	8
2	Morphology of nanostructures formed on the van der Waals surface of GaSe layered crystals annealed in sulfur vapor. <i>Physics of the Solid State</i> , 2011 , 53, 2154-2159	0.8	7
1	High-Performance Phototransistors by Alumina Encapsulation of a 2D Semiconductor with Self-Aligned Contacts. <i>Advanced Electronic Materials</i> , 2100954	6.4	0